

Access DB# 98635

SEARCH REQUEST FORM

Scientific and Technical Information Center

Requester's Full Name: Nicole Barreca Examiner #: 76619 Date: 6/26/03
 Art Unit: 1756 Phone Number 308-796-8 Serial Number: 10/042 278
 Mail Box and Bldg/Room Location: CP3 Results Format Preferred (circle): PAPER DISK E-MAIL
9D-29

If more than one search is submitted, please prioritize searches in order of need.

 Please provide a detailed statement of the search topic, and describe as specifically as possible the subject matter to be searched. Include the elected species or structures, keywords, synonyms, acronyms, and registry numbers, and combine with the concept or utility of the invention. Define any terms that may have a special meaning. Give examples or relevant citations, authors, etc. if known. Please attach a copy of the cover sheet, pertinent claims, and abstract.

Title of Invention: Process for producing an image using a first minimum bottom antireflective coating
 Inventors (please provide full names): Mark Weisser Joseph Oberlander Medhat Tackly Ray Sakamuri

Earliest Priority Filing Date: 1/9/02 Ding-Lee Shui

For Sequence Searches Only Please include all pertinent information (parent, child, divisional, or issued patent numbers) along with the appropriate serial number.

a bottom antireflective (antireflection)
 Coating or BARC

comprising a terpolymer of

(1)*N-methylmaleimide ⁹³⁰⁻⁸⁸⁻¹

(2)*mevalonic lactone methacrylate (MLMA) ¹⁷⁷⁰⁸⁰⁻⁶⁷⁻⁹

and

(3)* 2-methyladamantyl methacrylate ¹⁷⁷⁰⁸⁰⁻⁶⁷⁻⁰

Nothing with all 3 monomers together; printed out (MAdMA)
 whatever ~~antireflective~~ antireflective art there was for 2 of the 3 recited
 monomers together

STAFF USE ONLY

	Type of Search	Vendors and cost where applicable
Searcher: <u>EJL</u>	NA Sequence (#) _____	STN _____
Searcher Phone #: _____	AA Sequence (#) _____	Dialog _____
Searcher Location: _____	Structure (#) <u>(1)</u>	Questel/Orbit _____
Date Searcher Picked Up: _____	Bibliographic <u>(1)</u>	Dr. Link _____
Date Completed: <u>7-8-03</u>	Litigation _____	Lexis/Nexis _____
Searcher Prep & Review Time: <u>5</u>	Fulltext _____	Sequence Systems _____
Clerical Prep Time: _____	Patent Family _____	WWW/Internet _____
Online Time: <u>60</u>	Other _____	Other (specify) _____

=> file reg

FILE 'REGISTRY' ENTERED AT 15:48:53 ON 08 JUL 2003
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=> d his

FILE 'HCAPLUS' ENTERED AT 15:26:05 ON 08 JUL 2003

L1 566 S WEISSER ?/AU
L2 229 S OBERLANDER ?/AU
L3 51 S TOUKHY ?/AU
L4 28 S SAKAMURI ?/AU
L5 191406 S DING LEE ?/AU OR DING ?/AU OR LEE ?/AU
L6 0 S L1 AND L2 AND L3 AND L4 AND L5
L7 80 S NEISSER ?/AU
L8 0 S L7 AND L2 AND L3 AND L4 AND L5
L9 0 S (L1 OR L7) AND L2
L10 1 S (L1 OR L7) AND L3
L11 0 S (L1 OR L7) AND L4
L12 3 S (L1 OR L7) AND L5
L13 0 S L2 AND L3
L14 0 S L2 AND L4
L15 0 S L2 AND L5
L16 0 S L3 AND L4
L17 0 S L3 AND L5
L18 2 S L4 AND L5
L19 6 S L9-L18
SEL L19 1-6 RN

FILE 'REGISTRY' ENTERED AT 15:31:23 ON 08 JUL 2003

L20 19 S E1-E19
L21 18 S L20 AND PMS/CI

FILE 'LREGISTRY' ENTERED AT 15:32:14 ON 08 JUL 2003

E ADAMANTINE/CN
L22 1 S E5
L23 198 S 638.8.1/RID

FILE 'REGISTRY' ENTERED AT 15:32:41 ON 08 JUL 2003

L24 2 S L20 AND L23
E N-METHYLMALIMIDE/CN
L25 1 S E3
L26 212 S 930-88-1/CRN
L27 128 S 177080-66-9/CRN
L28 491 S 177080-67-0/CRN
L29 0 S L26 AND L27 AND L28
L30 0 S L26 AND L27
L31 0 S L26 AND L28
L32 41 S L27 AND L28
L33 32 S L32 NOT 3<NC

nothing with all 3 together

L34 57005 S 16.136.10/RID
L35 0 S L32 AND L34

FILE 'HCAPLUS' ENTERED AT 15:42:24 ON 08 JUL 2003

L36 107 S L33
L37 452108 S REFLECT? OR ANTIREFLECT?
L38 71 S L24
L39 1 S L36 AND L37
L40 1 S L36 AND L37
E COATING MATERIALS/CV
L41 235398 S E3
E COATING PROCESS/CV
L42 104893 S E3
L43 1 S L38 AND (L41 OR L42)
L44 1 S L36 AND (L41 OR L42)
L45 2 S L39 OR L40 OR L43 OR L44
L46 108 S (L36 OR L38) NOT L45

FILE 'REGISTRY' ENTERED AT 15:48:53 ON 08 JUL 2003

=> file hcaplus

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=> d l45 1-2 ibib abs hitstr hitind

L45 ANSWER 1 OF 2 HCAPLUS COPYRIGHT 2003 ACS

ACCESSION NUMBER: 1999:640906 HCAPLUS

DOCUMENT NUMBER: 131:272353

TITLE: Copolymers for coating and photoresist and their manufacture

INVENTOR(S): Fujiwara, Tadayuki; Tooyama, Masayuki; Wakisaka, Yukiya; Nishida, Koji; Yanagase, Akira

PATENT ASSIGNEE(S): Mitsubishi Rayon Co., Ltd., Japan

SOURCE: PCT Int. Appl., 29 pp.

CODEN: PIXXD2

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
-----	---	-----	-----	-----
WO 9950322	A1	19991007	WO 1999-JP1550	19990326
W: JP, KR, US				
RW: AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE				
EP 1074566	A1	20010207	EP 1999-910721	19990326
R: DE, FR, GB				

PRIORITY APPLN. INFO.:

JP 1998-82186	A	19980327
JP 1998-82187	A	19980327
JP 1998-82188	A	19980327
JP 1999-66615	A	19990312
WO 1999-JP1550	W	19990326

AB Copolymers for use in a coating material or a resist compn. are obtained by polymg. at least a monomer having an alicyclic skeleton and a monomer having a lactone skeleton and are characterized by having a distribution of the content of units derived from the lactone-contg. monomer in a copolymer within -10 to 10 mol% based on the av. content of the units in the whole copolymer. The copolymers have good adhesion to highly polar surfaces, such as metal surfaces, hydrophobicity, heat resistance, and satisfactory soly. in common solvents for coating materials and resists.

IT 177080-68-1P 245358-17-2P

(copolymers for coating and photoresist and their manuf.)

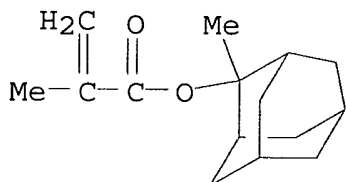
RN 177080-68-1 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl ester, polymer with tetrahydro-4-methyl-2-oxo-2H-pyran-4-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 177080-67-0

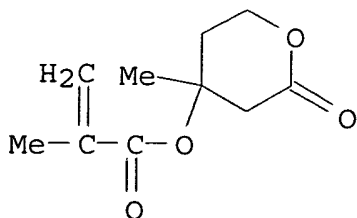
CMF C15 H22 O2



CM 2

CRN 177080-66-9

CMF C10 H14 O4



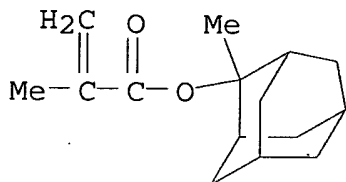
RN 245358-17-2 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, methyl ester, polymer with
2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl 2-methyl-2-propenoate and
tetrahydro-4-methyl-2-oxo-2H-pyran-4-yl 2-methyl-2-propenoate (9CI)
(CA INDEX NAME)

CM 1

CRN 177080-67-0

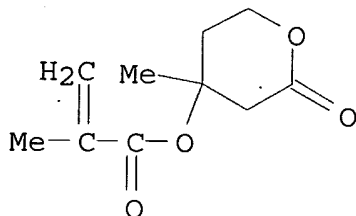
CMF C15 H22 O2



CM 2

CRN 177080-66-9

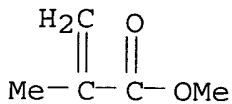
CMF C10 H14 O4



CM 3

CRN 80-62-6

CMF C5 H8 O2



IC ICM C08F220-16

ICS C08F220-26; C09D133-00; G03F007-039

CC 35-4 (Chemistry of Synthetic High Polymers)

Section cross-reference(s): 42, 74

IT Coating materials

Photoresists

(copolymers for coating and photoresist and their manuf.)

IT 177080-68-1P 195000-64-7P 195000-67-0P 195000-69-2P
210816-43-6P 245056-49-9P 245358-14-9P 245358-15-0P
245358-17-2P 245358-18-3P 245358-19-4P 245358-20-7P

(copolymers for coating and photoresist and their manuf.)

REFERENCE COUNT: 7 THERE ARE 7 CITED REFERENCES AVAILABLE FOR
THIS RECORD. ALL CITATIONS AVAILABLE IN
THE RE FORMAT

L45 ANSWER 2 OF 2 HCAPLUS COPYRIGHT 2003 ACS

ACCESSION NUMBER: 1998:776506 HCAPLUS

DOCUMENT NUMBER: 130:146062

TITLE: Lithographic performance of a dry-etch stable
methacrylate resist at 193 nmAUTHOR(S): Dammel, R. R.; Ficner, S.; Oberlander, J.;
Klauck-Jacobs, A.; Padmanaban, M.; Khanna, D.
N.; Durham, D. L.CORPORATE SOURCE: AZ Electronic Materials, Clariant Corporation,
Somerville, NJ, 08876, USASOURCE: Proceedings of SPIE-The International Society
for Optical Engineering (1998), 3333(Pt. 1,
Advances in Resist Technology and Processing
XV), 144-151PUBLISHER: CODEN: PSISDG; ISSN: 0277-786X
SPIE-The International Society for Optical
Engineering

DOCUMENT TYPE: Journal

LANGUAGE: English

AB High resolu. performance down to the 0.13 .mu.m level is
demonstrated in a methacrylate resist with pendent polycyclic side
groups. The best performance is achieved with a bottom coat
although interactions with the resist were still obsd. which led to
the presence of scum in fine lines and to a large dose change
relative to Si. The demonstrated dry etch rate of the resist is
.apprx.10% higher than APEX-E; predictions based on the ring
parameter would led one to expect a more favorable etch rate. The
obsd. discrepancy led one to speculate on possible exposure of the
resist by the plasma environment and loss of the etch resistant
polycyclic unit through evapn.

IT 177080-68-1
(AZ EXP AX1000; lithog. performance of dry-etch stable
methyladamantane methacrylate-mevalonic lactone methacrylate
copolymer-based AZ EXP AX1000 resist at 193 nm)

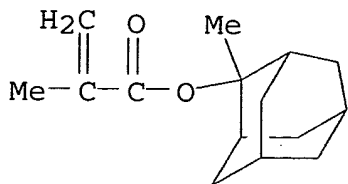
RN 177080-68-1 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-methyltricyclo[3.3.1.1^{3,7}]dec-2-yl
ester, polymer with tetrahydro-4-methyl-2-oxo-2H-pyran-4-yl
2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 177080-67-0

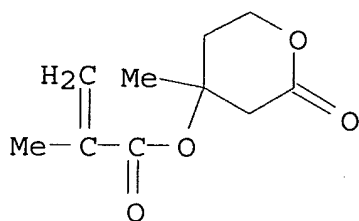
CMF C15 H22 O2



CM 2

CRN 177080-66-9

CMF C10 H14 O4



CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

IT 177080-68-1

(AZ EXP AX1000; lithog. performance of dry-etch stable methyladamantane methacrylate-mevalonic lactone methacrylate copolymer-based AZ EXP AX1000 resist at 193 nm)

IT 195460-14-1, AZ BARLiII

(antireflective coating; lithog. performance of dry-etch stable methyladamantane methacrylate-mevalonic lactone methacrylate copolymer-based AZ EXP AX1000 resist at 193 nm)

REFERENCE COUNT: 11 THERE ARE 11 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> d 146 1-108 ti

(monomers #2 and #3 together but not necessarily "antireflective")

L46 ANSWER 1 OF 108 HCAPLUS COPYRIGHT 2003 ACS

TI Positive-working resist composition containing specific fluorine group-containing resin

L46 ANSWER 2 OF 108 HCAPLUS COPYRIGHT 2003 ACS

TI Hybrid cycloolefin-maleic anhydride copolymers for 193 nm lithography

- L46 ANSWER 3 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified positive resists forming defect-free patterns by deep-UV lithography using F2 excimer lasers
- L46 ANSWER 4 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition containing fluoro-substituted nitrogen compound
- L46 ANSWER 5 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Photoresist composition for deep UV radiation containing image deterioration-preventing additive
- L46 ANSWER 6 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Pattern formation method
- L46 ANSWER 7 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Pattern formation method
- L46 ANSWER 8 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive photoresist composition
- L46 ANSWER 9 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Activation energies for deprotection reaction of chemically amplified resists: a study using in-situ FT-IR spectroscopy
- L46 ANSWER 10 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Process for producing film forming resins for photoresist compositions
- L46 ANSWER 11 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI E-beam curing effects on the etch and CD-SEM stability of 193-nm resists
- L46 ANSWER 12 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Illumination, acid diffusion, and process optimization considerations for 193-nm contact hole resists
- L46 ANSWER 13 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresists with high sensitivity and good resolution on development
- L46 ANSWER 14 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresists with high sensitivity and good resolution on development
- L46 ANSWER 15 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working chemically amplified photoresist composition
- L46 ANSWER 16 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI High-performance resist materials for ArF excimer laser and electron-beam lithography

- L46 ANSWER 17 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified positive-working photoimaging compositions for photofabrication by excimer lasers with high sensitivity and resolution
- L46 ANSWER 18 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Etch properties of 193nm resists: issues and approaches
- L46 ANSWER 19 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Optimization of 193 nm contact hole resists for 100 nm node
- L46 ANSWER 20 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Method for purifying resins for chemically amplified photoresists and resins thereby
- L46 ANSWER 21 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition containing alkylene glycol alkyl ether
- L46 ANSWER 22 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive resist composition
- L46 ANSWER 23 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified photoresists, resins therefor, preparation thereof, and semiconductor device fabrication thereby
- L46 ANSWER 24 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working resist compositions with high sensitivity and resolution
- L46 ANSWER 25 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working resist compositions with high sensitivity and resolution
- L46 ANSWER 26 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified positive-working photoresist compositions for excimer laser development with high sensitivity and resolution
- L46 ANSWER 27 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive photosensitive composition
- L46 ANSWER 28 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive photosensitive composition for photofabrication using deep UV ray
- L46 ANSWER 29 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Photoresist composition for deep UV and process thereof
- L46 ANSWER 30 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Copolymer having specific terminal groups for chemically amplified photoresist composition

- L46 ANSWER 31 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI CD changes of 193-nm resists during SEM measurement
- L46 ANSWER 32 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Novel hybrid copolymers of cycloolefin/maleic anhydride (COMA)/methacrylate for 193-nm resist compositions
- L46 ANSWER 33 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive photoresists showing minimized dependency on pattern density for deep-UV photolithography
- L46 ANSWER 34 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Pattern-forming positive-working photoresist and its pattern formation by exposure to 1-30 nm or 110-180 nm light
- L46 ANSWER 35 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemical amplification-type photoresist composition and patterning method
- L46 ANSWER 36 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified positive photoresists with superior resolution for deep-UV lithography
- L46 ANSWER 37 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition containing acetylene alcohol derivative
- L46 ANSWER 38 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition containing dialkylcarboxylic amide
- L46 ANSWER 39 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Materials and resists for 193 and 157 nm applications
- L46 ANSWER 40 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working chemically amplified photoresist composition
- L46 ANSWER 41 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for production of electric parts such as semiconductor substrate with contact holes
- L46 ANSWER 42 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for semiconductor device fabrication
- L46 ANSWER 43 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition
- L46 ANSWER 44 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Photoresist composition for deep UV radiation
- L46 ANSWER 45 OF 108 HCAPLUS COPYRIGHT 2003 ACS

- TI Positive-working resist composition
- L46 ANSWER 46 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemical amplification-type resist compositions, their manufacture, and pattern formation using them
- L46 ANSWER 47 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working resist composition
- L46 ANSWER 48 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified photoresist compositions and process for the formation of stable photoresist patterns
- L46 ANSWER 49 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working silicone-containing photosensitive compositions
- L46 ANSWER 50 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far ultraviolet ray exposure
- L46 ANSWER 51 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far ultraviolet ray exposure
- L46 ANSWER 52 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far ultraviolet ray exposure
- L46 ANSWER 53 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far ultraviolet ray exposure
- L46 ANSWER 54 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified resist composition
- L46 ANSWER 55 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Manufacturing method of copolymers using chain transfer agents for chemically amplified photoresists
- L46 ANSWER 56 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Manufacture of acrylic copolymer by using chemically amplified photoresist
- L46 ANSWER 57 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photosensitive composition
- L46 ANSWER 58 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Far-UV positive-working photoresist composition
- L46 ANSWER 59 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working chemical amplification photoresist composition for far-ultraviolet ray exposure

- L46 ANSWER 60 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Argon fluoride excimer laser-sensitive positive-working photoresist composition
- L46 ANSWER 61 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Excimer laser-sensitive positive-working photoresist composition
- L46 ANSWER 62 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Argon fluoride excimer laser-sensitive positive-working photoresist composition
- L46 ANSWER 63 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Argon fluoride excimer laser-sensitive positive-working photoresist composition
- L46 ANSWER 64 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Application of photodecomposable base concept to 193-nm resists
- L46 ANSWER 65 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working resist composition
- L46 ANSWER 66 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist compositions containing photosensitive acid generator.
- L46 ANSWER 67 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Photoresist composition containing photosensitive acid generator.
- L46 ANSWER 68 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition containing photosensitive acid generator.
- L46 ANSWER 69 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Far UV-sensitive positive-working photoresist compositions
- L46 ANSWER 70 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Method for fine pattern formation for semiconductor device fabrication
- L46 ANSWER 71 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition containing polymer having sulfonate group
- L46 ANSWER 72 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Sensitized transparent photobase additive for 193 nm lithography
- L46 ANSWER 73 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Layer-specific resists for 193 nm lithography
- L46 ANSWER 74 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far UV exposure

- L46 ANSWER 75 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working silicon-containing photosensitive composition
- L46 ANSWER 76 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Pattern formation using positive-working photoresist
- L46 ANSWER 77 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far UV ray exposure
- L46 ANSWER 78 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photosensitive composition containing lactone methacrylate copolymer
- L46 ANSWER 79 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far UV ray exposure
- L46 ANSWER 80 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far ultraviolet ray exposure
- L46 ANSWER 81 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photoresist composition for far ultraviolet ray exposure
- L46 ANSWER 82 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI ArF excimer laser-sensitive positive-working photoresist composition
- L46 ANSWER 83 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Theoretical calculation of photoabsorption of various polymers in an extreme ultraviolet region
- L46 ANSWER 84 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working resist composition suited for use in deep UV ray exposure
- L46 ANSWER 85 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working resist composition suited for use in deep ultraviolet ray exposure
- L46 ANSWER 86 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working resist composition suited for use in deep ultraviolet ray exposure
- L46 ANSWER 87 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Resist composition and resist pattern formation using same
- L46 ANSWER 88 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically amplified resist material and method for pattern formation using same
- L46 ANSWER 89 OF 108 HCAPLUS COPYRIGHT 2003 ACS

- TI Thermal phenomena in acrylic 193-nm resists
- L46 ANSWER 90 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Structural design of new alicyclic acrylate polymers with androstane moiety for 193-nm resist
- L46 ANSWER 91 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Resist solution providing highly precise patterns and manufacture of the solution
- L46 ANSWER 92 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Progress in polymers and photoresists applicable for 193 nm lithography
- L46 ANSWER 93 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Photoresist composition and pattern formation
- L46 ANSWER 94 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI 193 nm Lithography with novel highly transparent acid amplifier for chemically amplified resists
- L46 ANSWER 95 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI 193 nm Resists for deep sub-wavelength applications
- L46 ANSWER 96 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemically-amplified photoresist and its patterning forming pattern with good dry etching resistance
- L46 ANSWER 97 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive-working photosensitive composition
- L46 ANSWER 98 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Manufacture of adamantyl (meth)acrylate ester copolymers for chemically amplified resist materials
- L46 ANSWER 99 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Positive resist composition
- L46 ANSWER 100 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Resist containing nitrile compound and pattern formation using same
- L46 ANSWER 101 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Theoretical calculations of sensitivity of deprotection reactions for acrylic polymers for 193 nm lithography II: Protection groups containing an adamantyl unit
- L46 ANSWER 102 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Resist composition
- L46 ANSWER 103 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Chemical amplified resist composition and resist pattern formation using it

- L46 ANSWER 104 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Approach to high aspect ratio patterning using cleavable adamantyl resist
- L46 ANSWER 105 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Limits to etch resistance for 193-nm single-layer resists
- L46 ANSWER 106 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI A novel polymer for a 193-nm resist
- L46 ANSWER 107 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI Impact of 2-methyl-2-adamantyl group used for 193-nm single-layer resists
- L46 ANSWER 108 OF 108 HCAPLUS COPYRIGHT 2003 ACS
TI A new single-layer resist for 193-nm lithography